National Semiconductor is now part of Texas Instruments.

Search http://www.ti.com/ for the latest technical information and details on our current products and services.

THIS REVIS	SION DES		OF REVISION AS BEEN AUTH	ON (NOR) HORIZED FOR THE D	OOCUMENT LISTED.	1. DATE (YYMMDD) 98-09-09	Form Approved OMB No. 0704-0188
Public reporting	ing burden searching of information ggestions for no Operation agement a NOT RET HE GOVER STED IN IT	of for this collection is existing data source. The send comments row reducing this burd ons and Reports, 12 and Budget, Paperw URN YOUR COMPING (RNMENT ISSUING) TEM 2 OF THIS FOR	estimated to aves, gathering and egarding this buen, to Departments of the secondary of the	verage 2 hours per res d maintaining the data urden estimate or any ent of Defense, Washi avis Highway, Suite 12 Project (07040188), W TO EITHER OF THES 3 OFFICER FOR THE	ponse, including the ti needed, and complet other aspect of this co needed the control of the 04, Arlington, VA 222(ashington, DC 20503. E ADDRESSED. RET CONTRACT/ PROCU	me for reviewing ing and reviewing the blection of information information in information in its part of the control of the co	2. PROCURING ACTIVITY NO.
							3. DODAAC
4. ORIGINAT	ΓOR		Defense Sup 3990 East Br	(Street, City, State, Zip oply Center, Columbus road Street DH 43216-5000		5. CAGE CODE 67268	6. NOR NO. 5962-R141-98
a. TYPED NA Last)	AME (First,	Middle Initial,				7. CAGE CODE 67268	8. DOCUMENT NO. 5962-92147
9. TITLE OF MICROCIR		NT GITAL, ADVANCED I	BIPOLAR CMO	OS, OCTAL,	10. REVISION LETT	ER	11. ECP NO.
		/ITH NON-INVERTIN		ATE OUTPUTS,	a. CURRENT A	b. NEW B	
12. CONFIG	URATION	ITEM (OR SYSTEM) TO WHICH E	CP APPLIES			
13. DESCRIF	PTION OF	REVISION					
F F Sheet 12:	Revisions of Revisions of Revisions of Revision levalus and Revision lev	date column; add "98 vel block; change fro of sheets; for sheet ogic diagram; replace to the column of the column of the column; and the column of the column of the column of the column; and the column of the column of the column; and the column of the column; and the column of the column of the column; and the column; and the column; and the column of the column; and the column of the colum	B-09-09". om "A" to "B". 1 change from ' e with the follow 1A2 1A	_		2A3 2A4	
a. (X one)	X	R GOVERNMENT L		ed by the NOR may be	a used in manufacture		
	^			ceived before manufac			
				shall make above rev		-	
b. ACTIVITY	AUTHORI	IZED TO APPROVE				st, Middle Initial, Last)	
DSCC-VAC				e. SIGNATURE	Monica L. Poelking	,	f. DATE SIGNED
	tom Microe	electronics Team		Monica L. Poelking	1		(YYMMDD) 98-09-09
			ON				c. DATE SIGNED (YYMMDD)
DSCC-VAC	b. REVISION COMPLETED (Signature) DSCC-VAC Joseph A. Kerby						

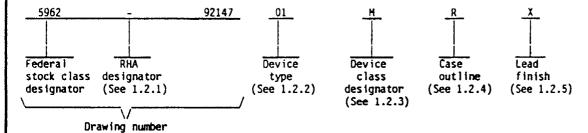
NOTICE OF F	REVISION (NOR)		1. DATE (YYMMDD)	Form Approved OMB No. 0704-0188
This revision described below has been	authorized for the documen	t listed.	94-06-15	
Public reporting burden for this collect the time for reviewing instructions, se data needed, and completing and review this burden estimate or any other aspec	ction is estimated to average earching existing data source ing the collection of inform ct of this collection of inf	e 2 hours per respect, gathering and ation. Send comme ormation, including	ents regarding	2. PROCURING ACTIVITY NO.
for reducing this burden, to Department for Information Operations and Reports, 22202-4302, and to the Office of Manage Washington, DC 20503. PLEASE DO NOT RE RETURN COMPLETED FORM TO THE GOVERNMENT ACTIVITY NUMBER LISTED IN ITEM 2 OF THI	ment and Budget, Paperwork TURN YOUR COMPLETED FORM TO ISSUING CONTRACTING OFFICE	my, Suite 1204, An Reduction Project EITHER OF THESE A R FOR THE CONTRACT	lington, VA (0704-0188), ADDRESSED. 7/ PROCURING	3. DODAAC
4. ORIGINATOR	b. ADDRESS (Street, City,	State, Zip Code)	5. CAGE CODE	6. NOR NO.
	Defense Electronics Sup 1507 Wilmington Pike	ply Center	67268 7. CAGE CODE	5962-R214-94 8. DOCUMENT NO.
a. TYPED NAME (First, Middle Initial, Last)	Dayton, OH 45444-5765		672 68	5962-92147
			0.200	3302 3211.
9. TITLE OF DOCUMENT		10. REVISION LET	TER	11. ECP NO.
MICROCIRCUIT, DIGITAL, ADVANCED BIPO BUFFER/DRIVER WITH NONINVERTING THRE	LAR CMOS, OCTAL	a. CURRENT	b. NEW	N/A
TTL COMPATIBLE INPUTS, MONOLITHIC SI		Initial	A	
12. CONFIGURATION ITEM (OR SYSTEM) TO W	HICH ECP APPLIES			
All				
13. DESCRIPTION OF REVISION				
Sheet 1: Revisions ltr column; add	пди			
Revisions description colu	mn; add "Changes in accordar	nce with NOR 5962-	R214-94".	
Revisions date column; add Revision level block; add	"94-06-15. "a"			
Rev status of sheets; for	sheets 1, 7 and 9, add "A".			
Chart 7. Table I input current his	h I change maximum limit	r from "+1.0 <i>u</i> A" t	o "+2.0 µA".	
Sheet 7: Table I, input current hig Table I, input current low	. i change maximum timit	110m -1.0 pa 40	- 2.0 μπ .	11.0 C - A11
Table I quiescent supply	current delta TTL input leve ata inputs, outputs enabled	is, Al., change	HIGH LINGS CINIT II OM	"1.5 MA" (.1" i
Revision level block; add	"A"	and control import		
Sheet 9: Table I, propagation delay	time, output enable, OEn to	mYn, tamu, chang	e maximum limits f	rom "4.6 ns"
to "5.5 ns" for s	time, output enable, OEn to ubgroup 9 and from "5.7 ns"	to "6.5 ns" for s	ubgroups 10 and 11	•
Revision level block; add				
Sheet 18: Table II, interim electri		olumn; delete "1"	for device class Q	1.
Revision level block; add	· · ·			
14. THIS SECTION FOR GOVERNMENT USE ONL	Y			
a. (X one) X (1) Existing d	ocument supplemented by the	NOR may be used i	n manufacture.	
	cument must be received before			s change.
i 	of master document shall mail			
b. ACTIVITY AUTHORIZED TO APPROVE CHANCE	****		First, Middle Initi	
D. ACITATII ADIMORTZED TO AFFROYE CHARC	IC TON GOTEMBIETT			-
DESC-ELDC		Monica L. Po	1	
d. TITLE	e. SIGNATURE		f. DATE SIGNED (YYMMDD)	
Chief, Custom Microelectronics	Monica L. Poelking		94-06-15	
15a. ACTIVITY ACCOMPLISHING REVISION	b. REVISION COMPLETED (Sig	nature)	c. DATE SIGNED (YYMMDD)	
DESC-ELDC	Joseph A. Kerby		94-06-15	
1 0536-5500	1			

DESC-ELDC

								RE	VISI	ONS										
LTR					DF	SCRI	PTIO		V 1.01				DATE (YR-HO-DA)				APPROVED			
																1				,
SHEET																				
SHEET REV	15	16	17	18	19	20														
SHEET REV SHEET	15	16	17	18	19 V	20														
SHEET REV SHEET REV STAT	US	16	17	RE	V	20	1	2	3	4	5	6	7	8	9	10	11	12	13	14
SHEET REV SHEET REV STAT	us S	16	17	RE SH	L	3Y	1 ph A.	1	J		<u> </u>	SE EL	ECTR	ONIC	S SU	PPLY	CEN		13	14
SHEET REV SHEET REV STAT OF SHEET PMIC N/A STAND MII	US S DARD	I ZED		RE SH PREP	V EET	3Y Jose	<u> </u>	Kerby	<u> </u>	DI	EFENS	SE EL	L	ONIC	S SU HIO	PPLY 454	CEN'	TER	1	14
SHEET REV SHEET REV STATOF SHEET PMIC N/A STAND MII	US S DARDI ITAK AWIN	ZZD RY G	BLE	RE SH PREP	V EET ARED 1	3Y Jose Y Thoma	ph A.	Kerby	ti	MIC BII WI'	EFENS CROC POLA TH N	SE EL EIRC'EIRC'ER C'EIRC'EIRC'EIRC'EIRC'EIRC'EIRC'EIRC'EIR	ECTR DAYTO	ONIC ON, O	S SU 0HIO GITA TAL	PPLY 454 AL, BUF	CEN'44 ADVIFER	TER ANCE	D VER	,
REV SHEET REV STATIOF SHEET PMIC N/A STAND MIL DR. THIS DRAWIT FOR USE BY	DARDI JARDI JITAL AWIN ALL DE NCIES (NT OF (ZED RY G AVAILAI PARTHE	BLE	RE SH PREP CHEC	V EET ARED 6 EXED BY	BY Mo	ph A.	Kerby	ti	MIC BII WI'	CROC POLA TH N	SE EL [CIRC LR C. HON- LS,	LECTROAYTO	ONICON, O	S SU 0HIO GITA TAL	PPLY 454 L, BUF THRE	CEN'44 ADVIFERA	TER ANCE	D VER	,

1. SCOPE

- 1.1 <u>Scope</u>. This drawing forms a part of a one part one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes B, Q, and M) and space application (device classes S and V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of radiation hardness assurance (RHA) levels are reflected in the PIN.
 - 1.2 PIN. The PIN shall be as shown in the following example:



- 1.2.1 <u>RHA designator</u>. Device classes M, B, and S RHA marked devices shall meet the MIL-M-38510 specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 Device type(s). The device type(s) shall identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>
01	54ABT244	Octal buffers/drivers with three-state outputs, TTL compatible inputs

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
М	Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883 $$
B or S	Certification and qualification to MIL-M-38510
Q or V	Certification and qualification to MIL-I-38535

1.2.4 Case outline(s). The case outline(s) shall be as designated in MIL-STD-1835, and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
R	GDIP1-T20 or CDIP2-T20	20	Dual-in-line
5	GDFP2-F20 or CDFP3-F20	20	Flat pack
2	CQCC1-N2O	20	Square chip carrier

1.2.5 <u>Lead finish</u>. The lead finish shall be as specified in MIL-M-38510 for classes M, B, and S or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 2

```
1.3 Absolute maximum ratings. 1/2/3/
```

1.4 Recommended operating conditions. 2/ 3/

1.5 Digital logic testing for device classes Q and V.

Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012) - - - - XX percent 5/

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 3

Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

Unless otherwise noted, all voltages are referenced to GND.

^{3/} The limits for the parameters specified herein shall apply over the full specified V_{CC} range and case temperature range of -55°C to +125°C.

The input and output negative voltage ratings may be exceeded provided that the input and output clamp current ratings are observed.

⁵/ Values will be added when they become available.

2. APPLICABLE DOCUMENTS

2.1 <u>Government specifications, standards, bulletin, and handbook</u>. Unless otherwise specified, the following specifications, standards, bulletin, and handbook of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATIONS

MILITARY

MIL-M-38510

Microcircuits, General Specification for.

MIL-I-38535

Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

HILITARY

MIL-STD-480

Configuration Control-Engineering Changes, Deviations and Waivers.

MIL-STD-883

Test Methods and Procedures for Microelectronics.

MIL-STD-1835

Microcircuit Case Outlines

BULLETIN

MILITARY

MIL-BUL-103

- List of Standardized Military Drawings (SMD's).

HANDBOOK

MILITARY

MIL-HOBK-780

- Standardized Military Drawings.

(Copies of the specifications, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 Item requirements. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes B and S shall be in accordance with MIL-M-38510 and as specified herein. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535, the device manufacturer's Quality Management (QM) plan, and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 for device classes M, B, and S and MIL-I-38535 for device classes Q and V and herein.
 - 3.2.1 Case outline. The case outline shall be in accordance with 1.2.4 herein.
 - 3.2.2 <u>Terminal</u> connections. The terminal connections shall be as specified on figure 1.
 - 3.2.3 <u>Iruth table</u>. The truth table shall be as specified on figure 2.
 - 3.2.4 Logic diagram. The logic diagram shall be as specified on figure 3.
- 3.2.5 <u>Ground bounce waveforms and test circuit</u>. The ground bounce load circuit and waveforms shall be as specified on figure 4.
- 3.2.6 <u>Switching waveforms and test circuit</u>. The switching waveforms and test circuit shall be as specified on figure 5.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 4

- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range. Test conditions for these specified characteristics and limits are as specified in table I.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes B and S shall be in accordance with MIL-M-38510. Marking for device classes Q and V shall be in accordance with MIL-I-38535.
- 3.5.1 <u>Certification/compliance mark</u>. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes B and S shall be a "J" or "JAN" as required in MIL-M-38510. The certification mark for device classes Q and V shall be a "QML" as required in MIL-I-38535.
- 3.6 Certificate of compliance. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.3 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.2 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M the requirements of MIL-STD-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-I-38535 and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or device classes B and S in MIL-M-38510 or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M</u>. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-480.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device classes M, B, and S</u>. Device classes M, B, and S devices covered by this drawing shall be in microcircuit group number XX (see MIL-M-38510, appendix E).
- 3.11 <u>Serialization for device class S</u>. All device class S devices shall be serialized in accordance with MIL-M-38510.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 5

TABLE	I.	Electrical	performance	characteristics.
I WOL "		C 1CCC1 1CC1	per i si illarico	01101 00 001 100 100

Test and MIL-STD-883 test	Symbo 1	Test conditions $\frac{2}{}$ / $-55^{\circ}\text{C} \le \text{T}_{\text{C}} \le +125^{\circ}\text{C}$ $4.5 \text{ V} \le \text{V}_{\text{CC}} \le 5.5 \text{ V}$ unless otherwise specified	Device type	v _{cc}	Group A subgroups	Limi	its <u>3</u> /	Unit
method $\underline{1}/$	İ	unless otherwise specified				Min	Max	
High level output voltage 3006	V _{OH1}	For all inputs affecting output under test V _{IN} = 2.0 V or 0.8 V I _{OH} = -3 mA	All	4.5 V	1,2,3	2.5		V
	V _{OH2}	For all inputs affecting output under test VIN = 2.0 V or 0.8 V IOH = -3 mA	All	5.0 V	1,2,3	3.0		
	V _{ОНЗ}	For all inputs affecting output under test V _{IN} = 2.0 V or 0.8 V I _{OH} = -24 mA	All	4.5 V	1,2,3	2.0		
Low level output voltage 3007	V _{OL}	For all inputs affecting output under test VIN = 2.0 V or 0.8 V IOL = 48 mA	All	4.5 V	1,2,3		0.55	V
Three-state output leakage current high 3021	192 <u>4</u>	For control inputs affecting output under test V _{IN} = V _{IH} or V _{IL} V _{IH} = 2.0 V _I V _{IH} = 0.8 V _{OUT} = 2.7 V	All	5.5 V	1,2,3		10.0	μΑ
Three-state output leakage current low 3020	192 <u>1</u>	For control inputs affecting output under test V _{IN} = V _{IH} or V _{IL} V _{IH} = 0.8 V _{IL} = 0.5 V	All	5.5 V	1,2,3		-10.0	μА
Negative input clamp voltage 3022	V _{IC} -	For input under test I _{IN} = -18 mA	All	4.5 V	1.2.3		-1.2	V
Off-state leakage current	IOFF	For input or output under test V _{IN} or V _{OUT} = 4.5 V All other pins at 0.0 V	All	0.0 V	1		±100	µА
High-state leakage current	I CEX	For output under test VOUT = 5.5 V Outputs at high logic state	All	5.5 V	1.2.3		50	μ Α

See footnotes at end of table.

STANDARDIZED MILITARY DRAWING	SIZE A_		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 6

TABLE I. El	ectrical	performance	characteristics -	 continued.
-------------	----------	-------------	-------------------	--------------------------------

Test and MIL-STD-883 test	Symbo 1	Test conditions 2/ -55°C ≤ T _C ≤ +125°C 4.5 V ≤ V _{CC} ≤ 5.5 V	Device type	v _{cc}	Group A subgroups	Lia	nits 3/	Unit
method 1/		unless otherwise specified		ļ 		Min	Max	
Input current high 3010	I IH	For input under test VIN ** VCC	All	5.5 V	1,2,3		+1.0	μА
Input current low 3009	IIL	For input under test V _{IN} - GND	All	5.5 V	1,2,3		-1.0	Α μ
Output current 3011	I ₀	v _{OUT} - 2.5 v	All	5.5 V	1,2,3	-50	-180	mA
Quiescent supply current delta TTL input levels 3005	AI _{CC}	Data inputs Outputs enabled For input under test V _{IN} = 3.4 V For all other inputs V _{IN} = V _{CC} or GND	All	5.5 V	1,2,3		1.5	mA
		Data inputs Outputs disabled For input under test V _{IN} = 3.4 V For all other inputs V _{IN} = V _{CC} or GNO	All	5.5 V	1,2,3		50.0	μΑ
		Control inputs For input under test V _{IN} = 3.4 V For all other inputs V _{IN} = V _{CC} or GND	All	5.5 V	1,2,3		1.5	mA
Quiescent supply current output high 3005	Іссн	VIN - VSCA GND	All	5.5 V	1,2,3		250	μΑ
Quiescent supply current output low 3005	I CCL	VIN - VSC OF GND	All	5.5 V	1,2,3		30	mA
Quiescent supply current output three-state 3005	Iccz	VIN = VSCA OF GND	A11	5.5 V	1.2.3		250	μА

See footnotes at end of table.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 7

TABLE I. Electrical performance characteristics - continued.

Test and	Symbo 1	Test conditions 2/ -55°C ≤ T _C ≤ +125°C 4.5 V ≤ V _{CC} ≤ 5.5 V unless otherwise specified	Device type	ν _{CC}	Group A subgroups	Limi	ts <u>3</u> /	Umit
MIL-STD-883 test method <u>l</u> /		unless otherwise specified				Min	Max	
nput capacitance 3012	CIN	See 4.4.1b T _C = +25°C	All	5.0 V	4		11	pF
utput capacitance 3012	COUT	See 4.4.1b T _C = +25°C	All	5.0 V	4		16	p₽
ow level ground bounce noise	y _S LP	V _{IH} = 3.0 V V _{IL} = 0.0 V T _A = +25°C See figure 4	All	5.0 V	4		1200	шV
ow level ground bounce noise	89LV		All	5.0 V	4		-1800	ωV
ligh level V _{CC} bounce noise	V _{OHP}		All	5.0 V	4		1500	æV
High level V _{CC} bounce noise	V _{OHV}		ATT	5.0 V	4		-1100	mV
Functional test	9/	V _{IL} = 0.8 V V _{IH} = 2.0 V Vehify output V ₀ See 4.4.1d	A11	4.5 V	7,8	L	Н	
			All	5.5 V	7.8	L	н	
Propagation delay	tpLH	C. = 50 pF minimum. R. = 5000.	All	5.0 V	9	1.0	4.1	ns
3003	10/	See figure 5		4.5 V and 5.5 V	ł	1.0	5.3	
Propagation delay	t _{PHL}	C _t = 50 pF minimum, R _t = 500Ω,	All	5.0 V	9	1.0	4.2	ns
time, mAn to mYr 3003	10/	See figure 5		4.5 \ and 5.5 \	j	1.0	5.0	

See footnotes at end of table.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 8

TABLE I. <u>Electrical performance characteristics</u> - continued.

Test and MIL-STD-883 test	Symbol 1	Test conditions 2/ -55°C ≤ T _C ≤ +125°C 4.5 V ≤ V _{CC} ≤ 5.5 V unless otherwise specified	Device type	v _{CC}	Group A subgroups	Lim	its <u>3</u> /	Unit	
method <u>1</u> /	<u> </u>	unless otherwise specified				Min	Max		
Propagation delay time, output	t _{PZH}	C ₁ = 50 pF minimum, R ₁ = 500Ω,	All	5.0 V	9	1.1	4.6	ns	
enable, OEn to mYn 3003				10,11	0.8 5.7				
Propagation delay	t _{PZL}	C ₁ = 50 pF minimum, R ₁ = 5000.	All	5.0 V	9	2.1	5.6	ns	
enable, 0€n to mYn 3003	<u>10</u> /	See figure 5	See Figure 5		4.5 V and 5.5 V	10,11	1.2	7.9	
Propagation delay	t _{PHZ}	C _L = 50 pF minimum, R _L = 5000,	All	5.0 V	9	2.1	5.6	ns	
disable, OEn to mYn 3003	<u>10</u> /	See figure 5		4.5 V and 5.5 V	10.11	1.2	7.6		
Propagation delay time, out <u>put</u>	t _{PLZ}	C ₁ = 50 pF minimum, R ₁ = 500Q.	All	5.0 V	9	1.5	5.6	ns	
disable, OEn to mYn 3003	10/	Sèe figure 5		4.5 V and 5.5 V	10,11	1.0	7.9		

^{1/} For tests not listed in the referenced MIL-STD-883 (e.g. AI_{CC}), utilize the general test procedure of 883 under the conditions listed herein.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-92147
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 9

²/ Each input/output, as applicable shall be tested at the specified temperature, for the specified limits, to the tests in table I herein. Output terminals not designated shall be high level logic, low level logic, or open, except for all I_{CC} and ΔI_{CC} tests, where the output terminals shall be open. When performing these tests, the current meter shall be placed in the circuit such that all current flows through the meter. For input terminals not designated, V_{IN} = GND or V_{IN} \geq 3.0 V_{IN} .

^{3/} For negative and positive voltage and current values: The sign designates the potential difference in reference to GND and the direction of current flow respectively; and the absolute value of the magnitude, not the sign, is relative to the minimum and maximum limits, as applicable, listed herein. All devices shall meet or exceed the limits specified in table I at 4.5 V ≤ V_{CC} ≤ 5.5 V.

- 4/ This test shall be guaranteed, if not tested, to the limits specified in table I herein, when performed with control inputs that affect the state of the output under test at $V_{IN} = 0.8 \text{ V}$ or 2.0 V.
- 5/ Due to tester limitations, this test may be performed at $V_{
 m IH}$ = 3.0 V but shall be guaranteed at $V_{
 m IH}$ = 2.0 V.
- 6/ Not more than one output should be tested at one time, and the duration of the test condition should not exceed one second.
- This test may be performed either one input at a time (preferred method) or with all input pins simultaneously at VIN = VCC -2.1 V (alternate method). Classes B, S, Q, and V shall use the preferred method. When the test is performed using the alternate test method the maximum limit is equal to the number of inputs at a high TTL input level times 50 μ A or 1.5 mA, as applicable, and the preferred method and limits are guaranteed.
- B/ This test is for qualification only. Ground and V_{CC} bounce tests are performed on a non-switching (quiescent) output and are used to measure the magnitude of induced noise caused by other simultaneously switching outputs. The test is performed on a low noise bench test fixture. For the device under test, all outputs shall be loaded with 5000 of load resistance and a minimum of 50 pF of load capacitance (see figure 4). Only chip capacitors and resistors shall be used. The output load components shall be located as close as possible to the device outputs. It is suggested, that whenever possible, this distance be kept to less than 0.25 inches. Decoupling capacitors shall be placed in parallel from V_{CC} to ground. The values of these decoupling capacitors shall be determined by the device manufacturer. The low and high level ground and V_{CC} bounce noise is measured at the quiet output using a 1 GHz minimum bandwidth oscilloscope with a 500 input impedance.

The device inputs shall be conditioned such that all outputs are at a high nominal V_{OH} level. The device inputs shall then be conditioned such that they switch simultaneously and the output under test remains at V_{OH} as all other outputs possible are switched from V_{OH} to V_{OH} . V_{OHV} and V_{OHP} are then measured from the nominal V_{OH} level to the largest negative and positive peaks, respectively (see figure 4). This is then repeated with the same outputs not under test switching from V_{OH} to V_{OH} .

The device inputs shall be conditioned such that all outputs are at a low nominal V_{OL} level. The device inputs shall then be conditioned such that they switch simultaneously and the output under test remains at V_{OL} as all other outputs possible are switched from V_{OL} to V_{OL} . V_{OLp} and V_{OLv} are then measured from the nominal V_{OL} level to the largest positive and negative peaks, respectively (see figure 4). This is then repeated with the same outputs not under test switching from V_{OH} to V_{OL} .

- 9/ Tests shall be performed in sequence, attributes data only. Functional tests shall include the truth table and other logic patterns used for fault detection. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2, herein. Functional tests shall be performed in sequence as approved by the qualifying activity on qualified devices. After incorporating allowable tolerances per MIL-STD-883, V_{IL} = 0.4 V and V_{IH} = 2.4 V. For outputs, L ≤ 0.8 V, H ≥ 2.0 V.
- 10/ For propagation delay tests, all paths must be tested.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 10

01
R,S,2
Terminal symbol
0E1 1A1 2Y4 1A2 2Y3 1A3 2Y2 1A4 2Y1 GMD 2A1 1Y4 2A2 1Y3 2A3 1Y2 2A4 1Y1 0E2 V

Pin descriptions				
Terminal symbol	Description			
mAn (m = 1 to 4, n = 1 to 2)	Data inputs			
OEn (n = 1 to 2)	Output enable controls			
mYn (m = 1 to 4, n = 1 to 2)	Outputs (non-inverting)			

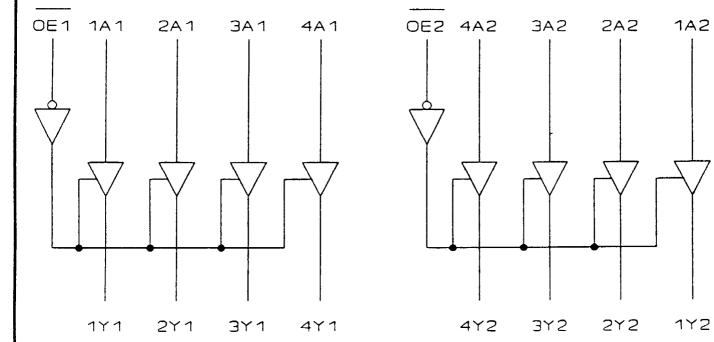
FIGURE 1. Terminal connections.

Device type 01				
Inputs				
0En	mAn	Output Y		
Ļ	Н	н		
H	X	L Z		

H = High voltage level
L = Low voltage level
X = Irrelevant
Z = Disabled

FIGURE 2. Truth table.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 11



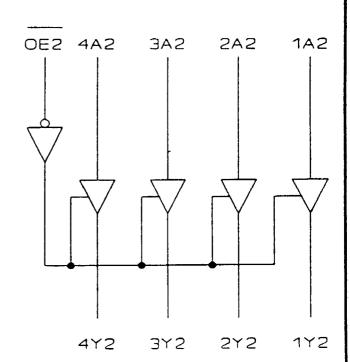
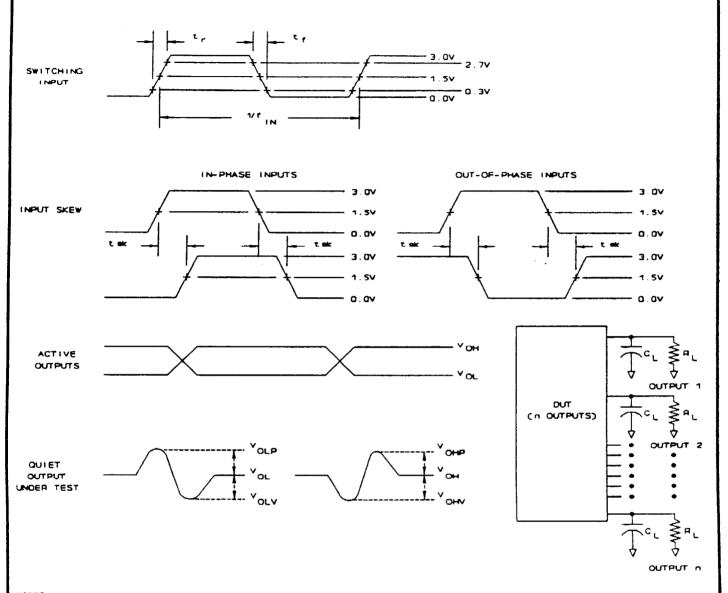


FIGURE 3. Logic diagram.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 12



HOTES:

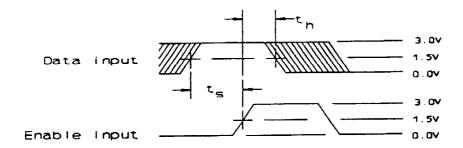
- includes a 47 pF chip capacitor (-0 percent, +20 percent) and at least 3 pF of equivalent capacitance from the test jig and probe.
- 2. R_1 = 4500 ±1 percent, chip resistor in series with a 500 termination. For monitored outputs, the 500 termination shall be the 500 characteristic impedance of the coaxial connector to the oscilloscope.
- 3. Input signal to the device under test:

 - a. V_{IN} = 0.0 V to 3.0 V; duty cycle = 50 percent; f_{IN} ≥ 1 MHz.
 b. t_r, t_f = 3 ns ±1.0 ns. For input signal generators incapable of maintaining these values of t_r and t_f, the 3.0 ns limit may be increased up to 10 ns, as needed, maintaining the ±1.0 ns tolerance and guaranteeing the results at 3.0 ns ±1.0 ns; skew between any two switching inputs signals (t_{sk}): ≤ 250 ps.

FIGURE 4. Ground bounce load circuit and waveforms.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 13

The shaded areas indicate when the input is permitted to change for predictable output performance.



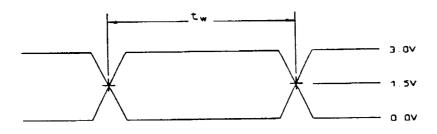
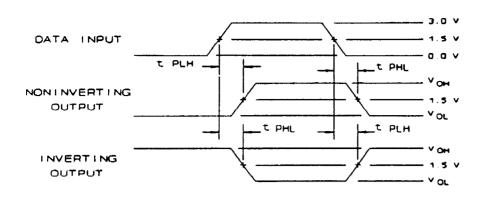
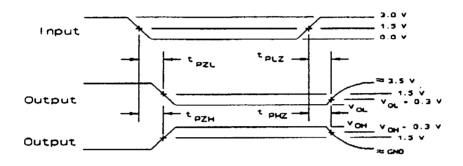
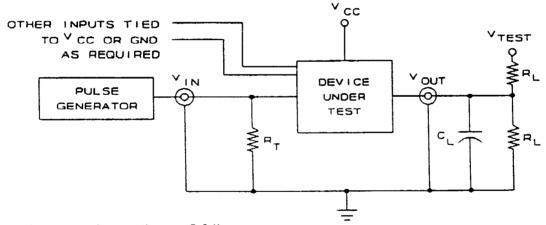


FIGURE 5. Switching waveforms and test circuit.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 14







NOTES:

When measuring t_{PLZ} and t_{PZL} : V_{TEST} = 7.0 V. When measuring t_{PHZ} , t_{PZH} , t_{PZH} and t_{PHL} : V_{TEST} = open. The t_{PZL} and t_{PLZ} reference waveform is for the output under test with internal conditions such that the output is at V_{OL} except when disabled by the output enable control. The t_{PZH} and t_{PLZ} reference waveform is for the output under test with internal conditions such that the output is at V_{OH} except when disabled by the output C_1 = 50 pF minimum or equivalent (includes test jig and probe capacitance). R_L^L = 5000 or equivalent. R_L^L = 5000 or equivalent.

- 5.
- 6.
- Input signal from pulse generator: V_{IN} = 0.0 V to 3.0 V; PRR \leq 10 MHz; $t_r \leq$ 2.5 ns; $t_r \leq$ 2.5 ns; t_r and t_f shall be measured from 0.3 to 2.7 V and 2.7 V to 0.3 V, respectively; duty cycle = 50 percent.
- Timing parameters shall be tested at a minimum input frequency of 1 MHz. The outputs are measured one at a time with one transition per measurement.

FIGURE 5. Switching waveforms and test circuit - Continued.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 15

4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. For device class M, sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein). For device class B, sampling and inspection procedures shall be in accordance with MIL-M-38510 and method 5005 of MIL-STD-883, except as modified herein. For device class S, sampling and inspection procedures shall be in accordance with MIL-M-38510, and methods 5005 and 5007 of MIL-STD-883, except as modified herein. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 and the device manufacturer's QM plan.
- 4.2 <u>Screening</u>. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes B and S, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to qualification and quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. The following additional criteria shall apply.

4.2.1 Additional criteria for device classes M, B, and S.

- a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C or D. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. For device classes B and S, the test circuit shall be submitted to the qualifying activity. For device classes M, B, and S, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - (3) For device class M, unless otherwise noted, the requirements for device class B in method 1015 of MIL-STD-883 shall be followed.

4.2.2 Additional criteria for device classes 0 and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535 and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
- b. Interim and final electrical test parameters shall be as specified in table II herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.

4.3 Qualification inspection.

- 4.3.1 Qualification inspection for device classes B and S. Qualification inspection for device classes B and S shall be in accordance with MIL-M-38510. Inspections to be performed shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5).
- 4.3.2 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5).

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 16

TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)			Subgroups (in accordance with MIL-I-38535, table III)	
	Device class M	Device class 8	Device class S	Device class Q	Device class V
Interim electrical parameters (see 4.2)		1	1	1	1
final electrical parameters (see 4.2)	1/ 1.2.3 7,8,9,10,11	1/ 1,2,3, 7,8,9,10,11	2/ 1,2,3, 7,8,9,10,11	1/ 1,2,3 7,8,9,10,11	<u>2</u> / 1,2,3 7,8,9,10,11
Group A test requirements (see 4.4)	1,2,3,4,7, 8,9,10,11	1,2,3,4,7, 8,9,10,11	1,2,3,4,7, 8,9,10,11	1,2,3,4,7, 8,9,10,11	1,2,3,4,7, 8,9,10,11
Group B end-point electrical parameters (see 4.4)			1,2,3,7,8, 9,10,11	·	
Group C end-point electrical parameters (see 4.4)	1,2,3	1,2,3		1,2,3	1,2,3
Group D end-point electrical parameters (see 4.4)	1,2,3	1,2,3	1,2,3	1,2,3	1,2,3
Group E end-point electrical parameters (see 4.4)	1,7,9	1,7,9	1,7,9	1,7,9	1,7,9

¹/ PDA applies to subgroup 1.

- 4.3.3 <u>Electrostatic discharge sensitivity qualification inspection</u>. Electrostatic discharge sensitivity (ESDS) testing shall be performed in accordance with MIL-STD-883, method 3015. ESDS testing shall be measured only for initial qualification and after process or design changes which may affect ESDS classification.
- 4.4 <u>Conformance inspection</u>. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Quality conformance inspection for device classes B and S shall be in accordance with MIL-M-38510 and as specified herein. Inspections to be performed for device classes M, B, and S shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. C_{IN} and C_{OUT} shall be measured only for initial qualification and after process or design changes which may affect capacitance. C_{IN} and C_{OUT} shall be measured between the designated terminal and GND at a frequency of 1 MHz. This test may be performed at 10 MHz and guaranteed, if not tested, at 1 MHz. The DC bias for the pin under test (V_{BIAS}) = 2.5 V or 3.0 V. For C_{IN} and C_{OUT} , test all applicable pins on three devices with zero failures.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-92147
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 17

 $[\]overline{2}$ / PDA applies to subgroups 1 and 7.

c. Ground and V_{CC} bounce tests are required for all device classes. These tests shall be performed only for initial qualification, after process or design changes which may affect the performance of the device, and any changes to the test fixture. V_{OLP}, V_{OLY}, V_{OHP}, and V_{OHY} shall be measured for the worst case outputs of the device. All other outputs shall be guaranteed, if not tested to limits established for the worst case outputs. The worst case outputs tested are to be determined by the manufacturer. Test 5 devices assembled in the worst case package type supplied to this document. All other package types shall be guaranteed, if not tested to limits established for the worst case package. The package type to be tested shall be determined by the manufacturer. The device manufacturer will submit to DESC-EC data that shall include, all measured peak values for each device tested and detailed oscilloscope plots for each V_{OLY}, V_{OHP}, and V_{OHY} from one sample part per function. The plot shall contain the waveforms of both a switching output and the output under test.

Each device manufacturer shall test product on the fixtures they currently use. When a new fixture is used, the device manufacturer shall inform DESC-EC of this change and test the 5 devices on both the new and old test fixtures. The device manufacturer shall then submit to DESC-EC data from testing on both fixtures, that shall include, all measured peak values for each device tested and detailed oscilloscope plots for each $V_{\rm OLP}$, $V_{\rm OLP}$, $V_{\rm OLP}$, and $V_{\rm OHP}$ from one sample part per function. The plot shall contain the waveforms of both a switching output and the output under test."

- d. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table in figure 2 herein. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2, herein. For device classes B and S, subgroups 7 and 8 tests shall be sufficient to verify the truth table as approved by the qualifying activity. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).
- 4.4.2 <u>Group B inspection.</u> The group B inspection end-point electrical parameters shall be as specified in table II herein. Class S steady-state life (accelerated) shall be conducted using test condition D of method 1005 of MIL-STD-883. For device class S steady-state life tests, the test circuit shall be submitted to the qualifying activity.
- 4.4.3 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table II herein.
- 4.4.3.1 Additional criteria for device classes M and B. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A. B. C or D. For device class M. the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. For device class B, the test circuit shall be submitted to the qualifying activity. For device classes M and B, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - b. $T_A = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STO-883.
- 4.4.3.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's TRB in accordance with MIL-I-38535 and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
- 4.4.4 Group D inspection. Group D inspection shall be in accordance with table IV of method 5005 of MIL-STD-883. End-point electrical parameters shall be as specified in table II herein.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 18

- 4.4.5 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes B, S, Q, and V shall be M, D, R, and H and for device class M shall be M and D.
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. For device classes M, B, and S, the devices shall be subjected to radiation hardness assured tests as specified in MIL-M-38510 for the RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-M-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as specified in table I at T_A = +25°C, after exposure, to the subgroups specified in table II herein.
 - c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
 - 4.5 Methods of inspection. Methods of inspection shall be specified as follows:
- 4.5.1 <u>Voltage and current</u>. Unless otherwise specified, all voltages given are referenced to the microcircuit GND terminal. Currents given are conventional current and positive when flowing into the referenced terminal.
 - 5. PACKAGING
- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510 for device classes M. B. and S and MIL-I-38535 for device classes Q and V.
 - 6. NOTES
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
 - 6.1.2 Substitutability. Device classes B and Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMO's</u>. All proposed changes to existing SMO's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).
- 6.3 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.
- 6.4 Comments. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444, or telephone (513) 296-5377.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-M-38510 and MIL-STD-1331, and as follows:

GND - - - - - - - Ground zero voltage potential.

I_CC - - - - - - - - - - Quiescent supply current.

IIL - - - - - - - - Input current low.

IIH - - - - - - - - - Input current high.

TC - - - - - - - - - - - Ambient temperature.

VA - - - - - - - - - - Positive supply voltage.

CCC - - - - - - - - - - - - Negative input clamp voltage.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 19

6.6 One part - one part number system. The one part - one part number system described below has been developed to allow for transitions between identical generic devices covered by the four major microcircuit requirements documents (MIL-M-38510, MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The four military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all four documents, the OEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

Military documentation format	Example PIN under new system	Manufacturing source listing	Document listing
New MIL-M-38510 Military Detail Specifications (in the SMD format)	5962-XXXXXZZ(B or S)YY	QPL-38510 (Part 1 or 2)	MIL-BUL-103
New MIL-H-38534 Standardized Military Drawings	5962-XXXXXZZ(H or K)YY	QML-38534	MIL-BUL-103
New HIL-I-38535 Standardized Hilitary Drawings	5962-XXXXXZZ(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standardized Military Orawings.	5962-XXXXXZZ(H)YY	MIL-BUL-103	MIL-BUL-103

6.7 Sources of supply.

- 6.7.1 <u>Sources of supply for device classes B and S</u>. Sources of supply for device classes B and S are listed in QPL-38510.
- 6.7.2 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.
- 6.7.3 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

STANDARDIZED MILITARY DRAWING	SIZE A		5962-92147
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		REVISION LEVEL	SHEET 20

STANDARDIZED HILITARY DRAWING SOURCE APPROVAL BULLETIN

DATE:93-08-11

Approved sources of supply for SMO 5962-92147 are listed below for immediate acquisition only and shall be added to MIL-BUL-103 during the next revision. MIL-BUL-103 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DESC-EC. This bulletin is superseded by the next dated revision of MIL-BUL-103.

Standardized military drawing PIN	Vendor CAGE number	Vendor similar PIN <u>1</u> /
5962-9214701HRX	01295 18324	SNJ54ABT244J 54ABT244/BRA
5962-9214701MSX	01295 18324	SNJ54ABT244W 54ABT244/BSA
5962-9214701H2X	01295 18324	SNJ54ABT244FK 54ABT244/B2A

1/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number	Vendor name and address Texas Instruments Incorporated 13500 N. Central Expressway P.O. Box 655303 Dallas, TX 75265 Point of contact: I-20 at FM 1788 Midland, TX 79711-0448	
01295		
18324	Philips Semiconductor 830 Stewart Dr. Sunnyvale, CA 94088 Point of contact: 811 E. Arques Ave. P.O. Box 3409 Sunnyvale, CA 94088-3409	

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.